

ABSTRACT

INTEGRATED CIRCUIT SYSTEM EMPLOYING SELECTIVE EPITAXIAL GROWTH TECHNOLOGY

5 An integrated circuit system that includes: providing a substrate; depositing a dielectric on the substrate; depositing an isolation dielectric on the dielectric; forming a trench through the isolation dielectric and the dielectric to expose the substrate; depositing a dielectric liner over the integrated circuit system; processing the dielectric liner to form a trench spacer; and depositing an epitaxial growth within the trench that includes a crystalline orientation that is substantially identical to the substrate.

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Fig. 8